

General Description

The 160N03 uses Trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance.

Product Summary

BVDSS	R _{DS(on)} max.	ID
30V	2.5mΩ	160A

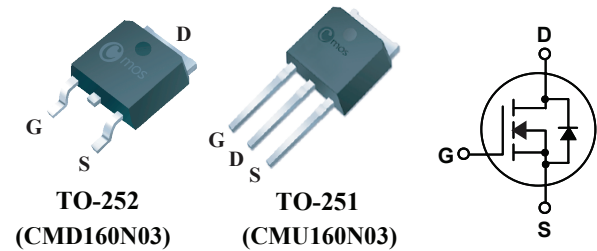
Applications

- Switching applications

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

TO-252/251 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	160	A
I _D @T _C =100°C	Continuous Drain Current	100	A
I _{DM}	Pulsed Drain Current	640	A
EAS	Single Pulse Avalanche Energy ¹	490	mJ
P _D @T _C =25°C	Total Power Dissipation	130	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient	---	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case	---	0.96	°C/W

Electrical Characteristics(T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =28A	---	2.1	2.5	mΩ
		V _{GS} =4.5V , I _D =25A	---	4.0	5.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V , V _{GS} =0V	---	---	1	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =20A	---	39	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	1.9	---	Ω
Q _g	Total Gate Charge	I _D =20A V _{DD} =15V V _{GS} =10V	---	73	---	nC
Q _{gs}	Gate-Source Charge		---	8	---	
Q _{gd}	Gate-Drain Charge		---	17	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =20V V _{GS} =10V R _G =3Ω , I _D =20A	---	17.4	---	ns
T _r	Rise Time		---	9.2	---	
T _{d(off)}	Turn-Off Delay Time		---	79	---	
T _f	Fall Time		---	17.4	---	
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz	---	3400	---	pF
C _{oss}	Output Capacitance		---	370	---	
C _{rss}	Reverse Transfer Capacitance		---	340	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	160	A
I _{SM}	Pulsed Source Current		---	---	640	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =20A , T _J =25°C	---	0.82	1.2	V

Note :

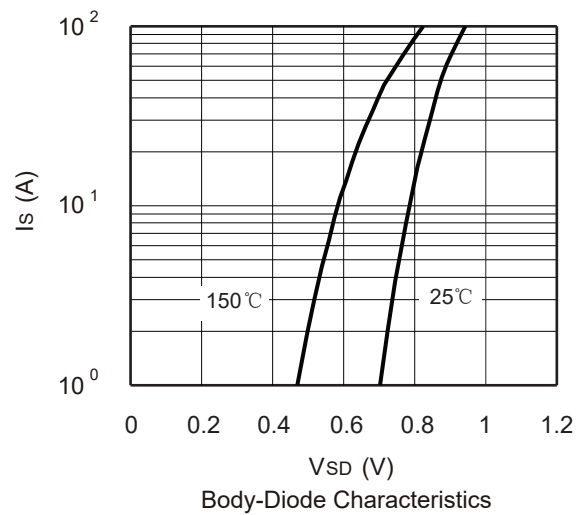
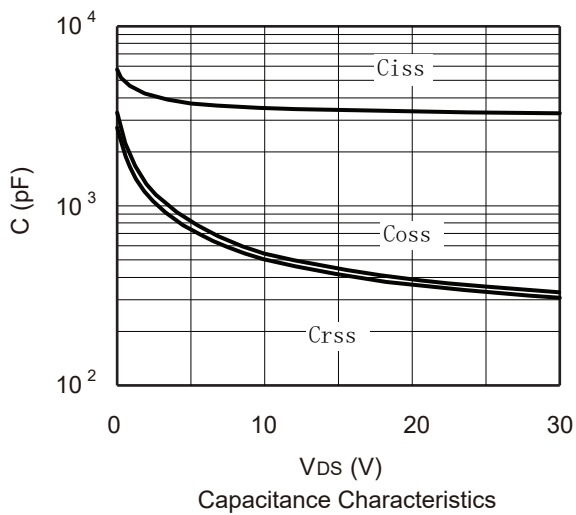
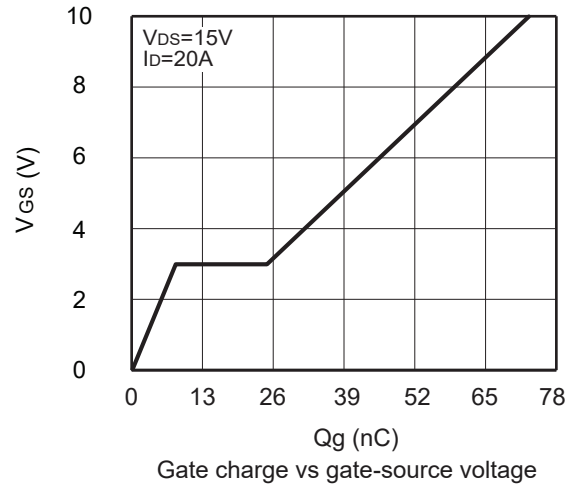
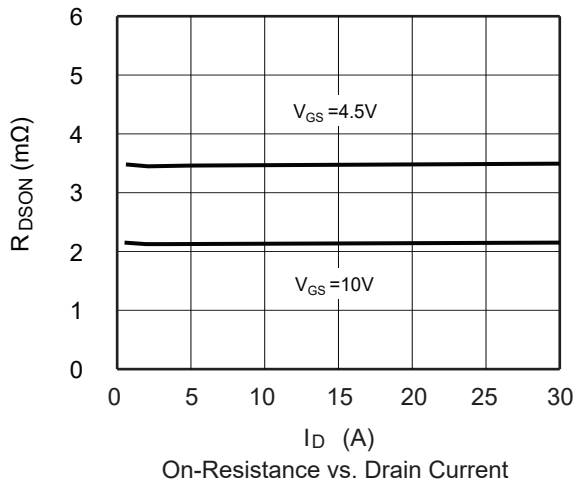
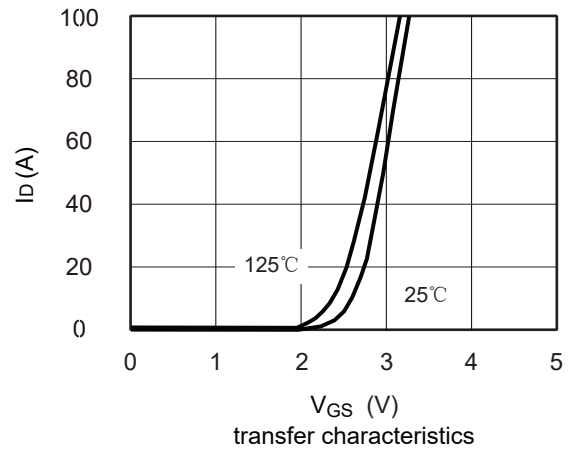
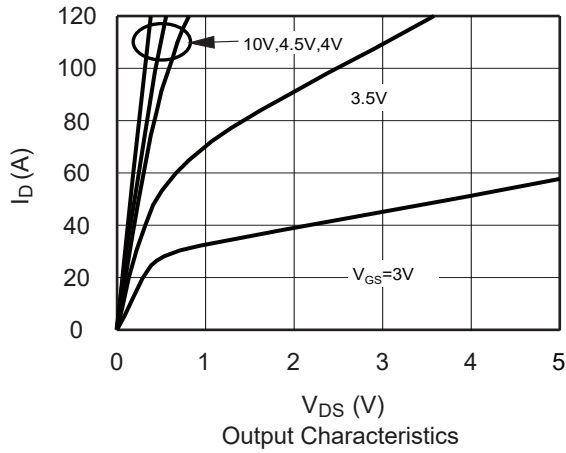
1.The EAS data shows Max. rating . The test condition is V_{DD}=25V , V_{GS}=10V , L=0.5mH , I_{AS}=44.3A.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

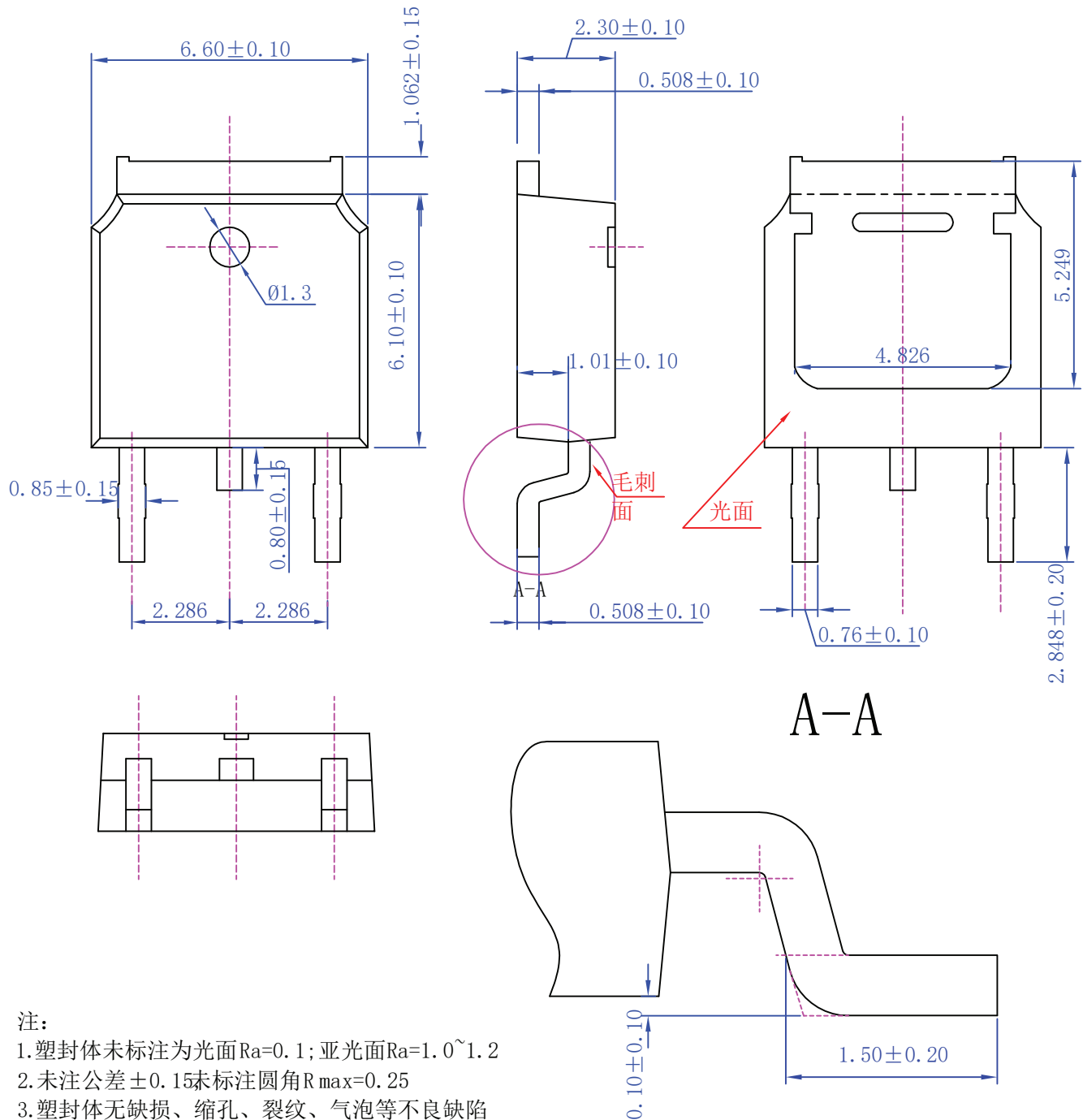
Typical Characteristics



Package Dimension

TO-252

Unit :mm



Package Dimension

TO-251A

Unit :mm

